ABSTRACT

A method for manufacturing an epitaxial wafer that can reduce occurrence of a surface defect or a slip formed on an epitaxial layer is provided. The manufacturing method is characterized by comprising: a smoothing step of controlling application of an etchant to a wafer surface in accordance with a surface shape of a silicon wafer to smooth the wafer surface; and an epitaxial layer forming step of forming an epitaxial layer formed of a silicon single crystal on the surface of the wafer based on epitaxial growth.